ABSTRACT

The present invention relates to a method for fabricating a semiconductor device. The method comprises the steps of: forming a gate line on a semiconductor substrate; forming a buffer layer and a spacer nitride film on the entire surface of the substrate including the gate line; selectively etching the buffer layer and the spacer nitride film in such a manner that they remain on both sides of the gate line; performing an ion implantation process using the remaining buffer layer and spacer nitride film as a barrier film to form junction regions in the semiconductor substrate at both sides of the gate line; forming an interlayer insulating film on the entire upper portion of the resulting substrate; selectively removing the interlayer insulating film to form contact holes exposing the upper surface of the junction regions; and forming contact plugs in the contact holes.